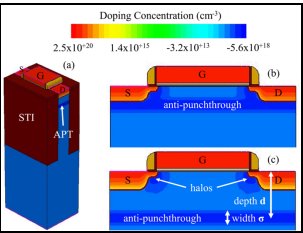


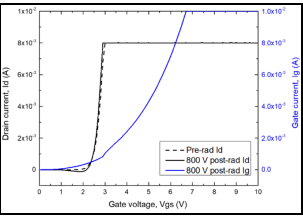
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By Gabriele Andreetta; Giulio Borghello; Federico Faccio; Simone Gerardin; Marta Bagatin; Alessandro Paccagnella

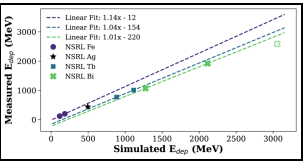
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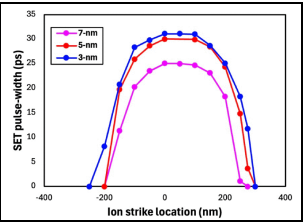
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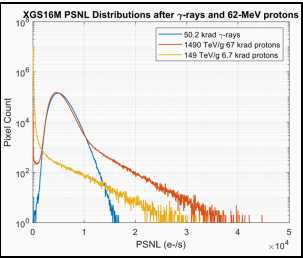
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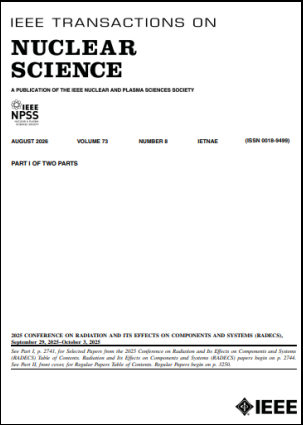
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A publication of the IEEE Nuclear and Plasma Sciences Society.

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